ABSTRACT OF DISCLOSURE

Thermoelectric material of (Bi, Sb)(Te, Se) system is produced through a liquid quenching method and an extrusion from a die unit having an inlet portion and an outlet portion crossing each other at 30 – 150 degrees so that the crystal grains have an average grain size equal to or less than 30 microns and (001) planes mostly oriented in parallel to a direction in which electric current to flow, thereby achieving the figure of merit equal to or greater than 3.0×10^{-3}/ K.

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